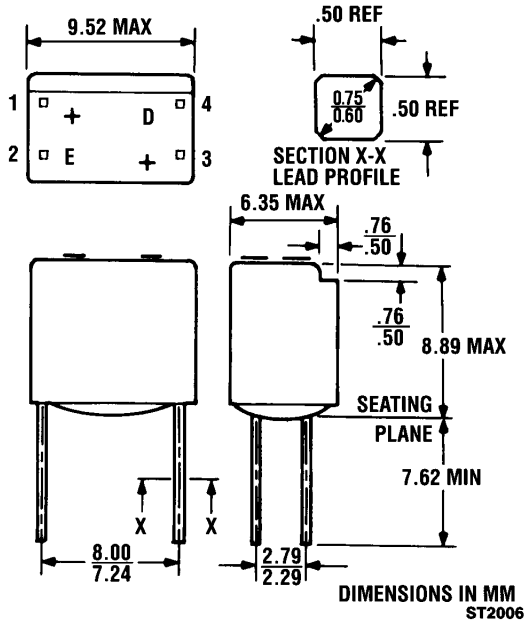


**PACKAGE DIMENSIONS**

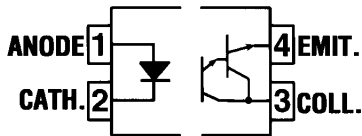


**DESCRIPTION**

The H24B series consists of a gallium arsenide infrared emitting diode coupled with a silicon phototransistor. The devices are housed in a low-cost plastic package with lead spacing compatible with a dual in-line package.

**FEATURES**

- 4-pin configuration
- Small package size and low cost
- UL recognized-file E51868
- High current transfer ratio



ST4004

*Equivalent Circuit*

**ABSOLUTE MAXIMUM RATINGS**

**TOTAL PACKAGE**

Storage temperature	.....	-55°C to 85°C
Operating temperature	.....	-55°C to 85°C
Lead solder temperature	.....	260°C for 5 sec

**INPUT DIODE**

Power dissipation (25°C ambient)	.....	100 mW
Derate linearly (above 25°C)	.....	1.67 mW/°C
Continuous forward current	.....	60 mA
Peak forward current (1 μs pulse, 300pps)	.....	3 A
Reverse voltage	.....	4 V

**DETECTOR**

Power dissipation (at 25°C ambient)	.....	150 mW
Derate linearly (above 25°C ambient)	.....	2.5 mW/°C
V <sub>CEO</sub>	.....	30 V
V <sub>ECC</sub>	.....	7 V
Continuous forward current	.....	100 mA